

2SA0720A (2SA720A)

Silicon PNP epitaxial planar type

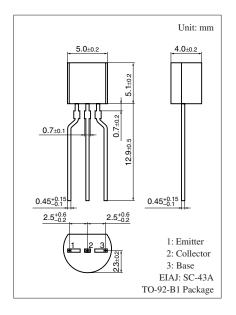
For low-frequency driver amplification Complementary to 2SC1318A

■ Features

- ullet High collector-emitter voltage (Base open) V_{CEO}
- Optimum for the driver stage of a low-frequency and 25 W to 30 W output amplifier

■ Absolute Maximum Ratings $T_a = 25$ °C

Parameter	Symbol	Rating	Unit	
Collector-base voltage (Emitter open)	V _{CBO}	-80	V	
Collector-emitter voltage (Base open)	V _{CEO}	-70	V	
Emitter-base voltage (Collector open)	V_{EBO}	-5	V	
Collector current	I_C	- 0.5	A	
Peak collector current	I_{CP}	-1	A	
Collector power dissipation	P _C	625	mW	
Junction temperature	T_{j}	150	°C	
Storage temperature	T_{stg}	-55 to +150	°C	



\blacksquare Electrical Characteristics $T_a = 25 ^{\circ}C \pm 3 ^{\circ}C$

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-base voltage (Emitter open)	V _{CBO}	$I_C = -10 \ \mu A, I_E = 0$	-80			V
Collector-emitter voltage (Base open)	V _{CEO}	$I_C = -2 \text{ mA}, I_B = 0$	-70			V
Emitter-base voltage (Collector open)	V_{EBO}	$I_E = -10 \mu A, I_C = 0$	-5			V
Collector-base cutoff current (Emitter open)	I_{CBO}	$V_{CB} = -20 \text{ V}, I_{E} = 0$			- 0.1	μΑ
Forward current transfer ratio *1	h _{FE1} *2	$V_{CE} = -10 \text{ V}, I_{C} = -150 \text{ mA}$	85		240	_
	h _{FE2}	$V_{CE} = -10 \text{ V}, I_{C} = -500 \text{ mA}$	40			_
Collector-emitter saturation voltage *1	V _{CE(sat)}	$I_C = -300 \text{ mA}, I_B = -30 \text{ mA}$		- 0.2	- 0.6	V
Base-emitter saturation voltage *1	V _{BE(sat)}	$I_C = -300 \text{ mA}, I_B = -30 \text{ mA}$		- 0.85	-1.50	V
Transition frequency	f_T	$V_{CB} = -10 \text{ V}, I_E = 50 \text{ mA}, f = 200 \text{ MHz}$		120		MHz
Collector output capacitance	C _{ob}	$V_{CB} = -10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$		20	30	pF
(Common base, input open circuited)						

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

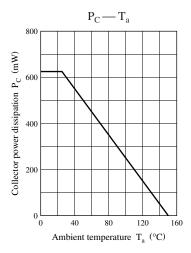
2. *1: Pulse measurment

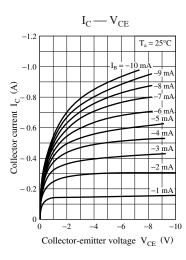
*2: Rank classification

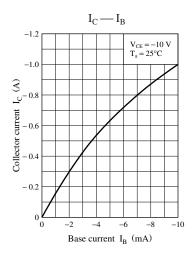
Rank	Q	R
h _{FE1}	85 to 170	120 to 240

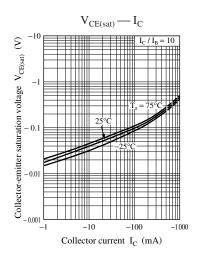
Note) The part number in the parenthesis shows conventional part number.

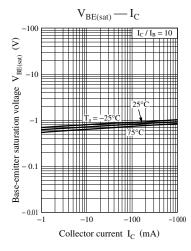
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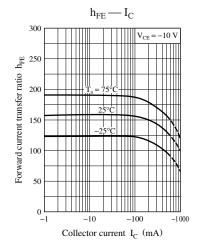


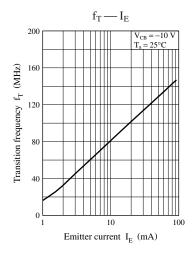


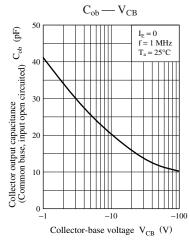


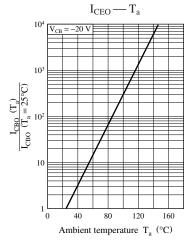












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